# N-Channel 250 V (D-S) MOSFET

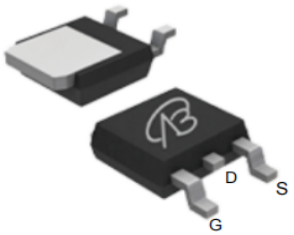
| PRODUCT SUMMARY | | |
|---|---|---|
| $V_{DS}$ (V) | 250 | |
| $R_{DS(on)}$ (Ω) | $V_{GS}$ = 10 V | 1.7 |
| $Q_g$ (Max.) (nC) | 8.0 | |
| $Q_{gs}$ (nC) | 1.6 | |
| $Q_{gd}$ (nC) | 4.3 | |
| Configuration | Single | |

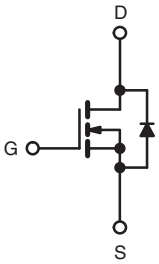
## FEATURES

- Surface mount
- Available in tape and reel
- Dynamic dV/dt rating
- Repetitive avalanche rated
- Fast switching
- Ease of paralleling
- Simple drive requirements

RoHS COMPLIANT
HALOGEN FREE Available

TO-252




N-Channel MOSFET

| ABSOLUTE MAXIMUM RATINGS ($T_C$ = 25 °C, unless otherwise noted) | | | | | |
|---|---|---|---|---|---|
| PARAMETER | | | SYMBOL | LIMIT | UNIT |
| Drain-Source Voltage | | | $V_{DS}$ | 250 | V |
| Gate-Source Voltage | | | $V_{GS}$ | ± 20 | |
| Continuous Drain Current | $V_{GS}$ at 10 V | $T_C$ = 25 °C | $I_D$ | 0.5 | A |
| | | $T_C$ = 100 °C | | 0.4 | |
| Pulsed Drain Current [a] | | | $I_{DM}$ | 1.5 | |
| Linear Derating Factor | | | | 0.025 | W/°C |
| Linear Derating Factor (PCB Mount) [e] | | | | 0.017 | |
| Single Pulse Avalanche Energy [b] | | | $E_{AS}$ | 50 | mJ |
| Repetitive Avalanche Current [a] | | | $I_{AR}$ | 0.79 | A |
| Repetitive Avalanche Energy [a] | | | $E_{AR}$ | 0.31 | mJ |
| Maximum Power Dissipation | $T_C$ = 25 °C | | $P_D$ | 3.1 | W |
| Maximum Power Dissipation (PCB Mount) [e] | $T_A$ = 25 °C | | | 2.0 | |
| Peak Diode Recovery dV/dt [c] | | | dV/dt | 4.8 | V/ns |
| Operating Junction and Storage Temperature Range | | | $T_J$, $T_{stg}$ | -55 to +150 | °C |
| Soldering Recommendations (Peak Temperature) [d] | for 10 s | | | 300 | |

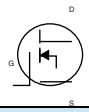
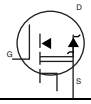
**Notes**

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
b. $V_{DD}$ = 50 V, starting $T_J$ = 25 °C, L = 128 mH, $R_g$ = 25 Ω, $I_{AS}$ = 0.79 A (see fig. 12).
c. $I_{SD} \leq 2.7$ A, dI/dt ≤ 65 A/μs, $V_{DD} \leq V_{DS}$, $T_J \leq 150$ °C.
d. 1.6 mm from case.
e. When mounted on 1" square PCB (FR-4 or G-10 material).

| THERMAL RESISTANCE RATINGS | | | | | |
|---|---|---|---|---|---|
| **PARAMETER** | **SYMBOL** | **MIN.** | **TYP.** | **MAX.** | **UNIT** |
| Maximum Junction-to-Ambient (PCB Mount) [a] | $R_{thJA}$ | - | - | 60 | °C/W |
| Maximum Junction-to-Case (Drain) | $R_{thJC}$ | - | - | 40 | |

**Note**

a. When mounted on 1" square PCB (FR-4 or G-10 material).

| **SPECIFICATIONS** ($T_J$ = 25 °C, unless otherwise noted) | | | | | | | |
|---|---|---|---|---|---|---|---|
| **PARAMETER** | **SYMBOL** | **TEST CONDITIONS** | | **MIN.** | **TYP.** | **MAX.** | **UNIT** |
| **Static** | | | | | | | |
| Drain-Source Breakdown Voltage | $V_{DS}$ | $V_{GS}$ = 0 V, $I_D$ = 250 μA | | 250 | - | - | V |
| $V_{DS}$ Temperature Coefficient | $\Delta V_{DS}/T_J$ | Reference to 25 °C, $I_D$ = 1 mA | | - | 0.39 | - | V/°C |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS}$ = $V_{GS}$, $I_D$ = 250 μA | | 3.0 | - | 5.0 | V |
| Gate-Source Leakage | $I_{GSS}$ | $V_{GS}$ = ± 20 V | | - | - | ± 100 | nA |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{DS}$ = 200 V, $V_{GS}$ = 0 V | | - | - | 25 | μA |
| | | $V_{DS}$ = 200 V, $V_{GS}$ = 0 V, $T_J$ = 125 °C | | - | - | 250 | |
| Drain-SourceOn-StateResistance | $R_{DS(on)}$ | $V_{GS}$=10V | $I_D$=0.47A [b] | - | 1.7 | - | Ω |
| Forward Transconductance | $g_{fs}$ | $V_{DS}$ = 50 V, $I_D$ = 0.47 A | | 0.50 | - | - | S |
| **Dynamic** | | | | | | | |
| Input Capacitance | $C_{iss}$ | $V_{GS}$ = 0 V, $V_{DS}$ = 25 V, f = 1.0 MHz, see fig. 5 | | - | 170 | - | pF |
| Output Capacitance | $C_{oss}$ | | | - | 42 | - | |
| Reverse Transfer Capacitance | $C_{rss}$ | | | - | 9.6 | - | |
| Total Gate Charge | $Q_g$ | $V_{GS}$ = 10 V | $I_D$ = 0.47 A, $V_{DS}$ = 200 V, see fig. 6 and 13 [b] | - | - | 8.2 | nC |
| Gate-Source Charge | $Q_{gs}$ | | | - | - | 1.8 | |
| Gate-Drain Charge | $Q_{gd}$ | | | - | - | 4.5 | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD}$ = 125 V, $I_D$ = 0.47 A, $R_g$ = 24 Ω, $R_D$ = 45 Ω, see fig. 10 [b] | | - | 7.0 | - | ns |
| Rise Time | $t_r$ | | | - | 7.6 | - | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | - | 16 | - | |
| Fall Time | $t_f$ | | | - | 7.0 | - | |
| Internal Drain Inductance | $L_D$ | Between lead, 6 mm (0.25") from package and center of die contact  | | - | 4.0 | - | nH |
| Internal Source Inductance | $L_S$ | | | - | 6.0 | - | |
| **Drain-Source Body Diode Characteristics** | | | | | | | |
| Continuous Source-Drain Diode Current | $I_S$ | MOSFET symbol showing the integral reverse p - n junction diode  | | - | - | 0.5 | A |
| Pulsed Diode Forward Current [a] | $I_{SM}$ | | | - | - | 1.5 | |
| Body Diode Voltage | $V_{SD}$ | $T_J$ = 25 °C, $I_S$ = 0.6A, $V_{GS}$ = 0 V [b] | | - | - | 2.0 | V |
| Body Diode Reverse Recovery Time | $t_{rr}$ | $T_J$ = 25 °C, $I_F$ = 1.8A, dI/dt = 100 A/μs [b] | | - | 70 | - | ns |
| Body Diode Reverse Recovery Charge | $Q_{rr}$ | | | - | 0.64 | 1.3 | μC |
| Forward Turn-On Time | $t_{on}$ | Intrinsic turn-on time is negligible (turn-on is dominated by $L_S$ and $L_D$) | | | | | |

**Notes**

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).

b. Pulse width ≤ 300 μs; duty cycle ≤ 2 %.

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

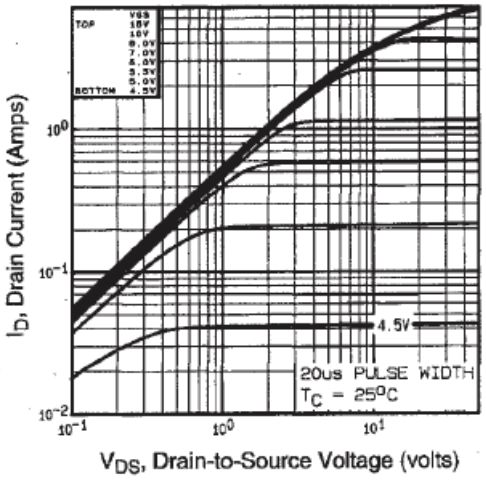



Fig. 1 - Typical Output Characteristics

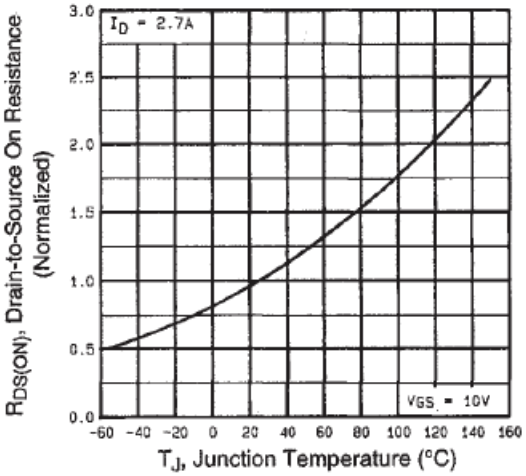



Fig. 4 - Normalized On-Resistance vs. Temperature

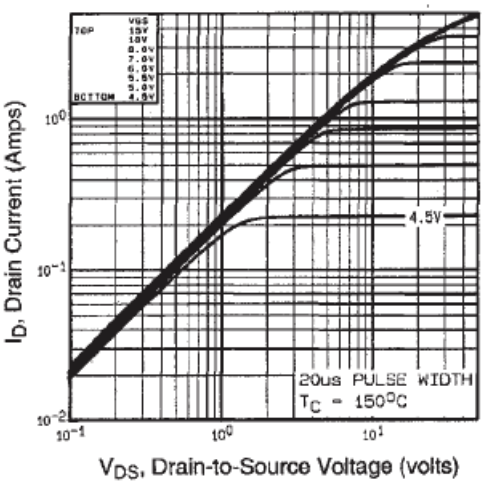



Fig. 2 - Typical Output Characteristics

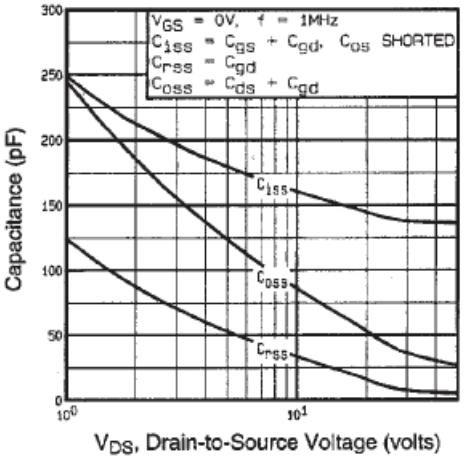



Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

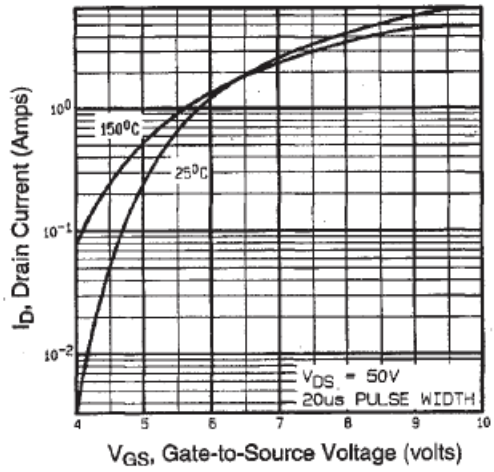



Fig. 3 - Typical Transfer Characteristics

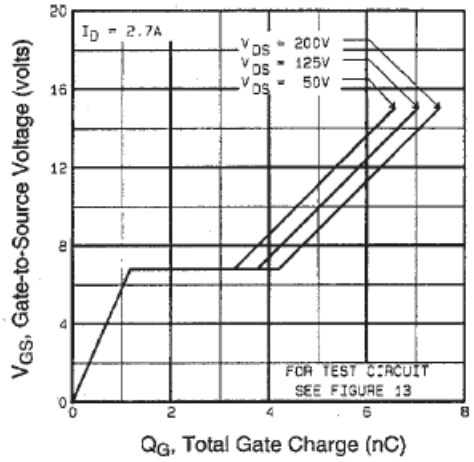



Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

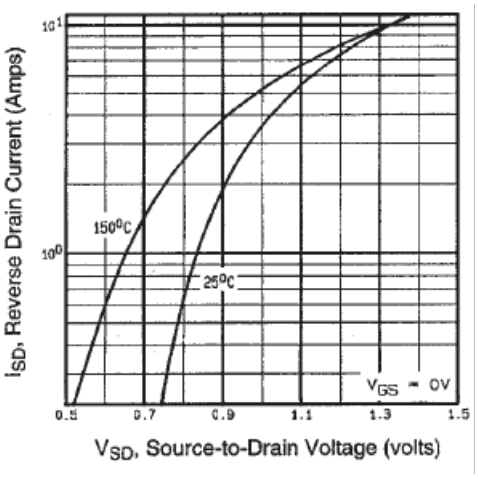



Fig. 7 - Typical Source-Drain Diode Forward Voltage

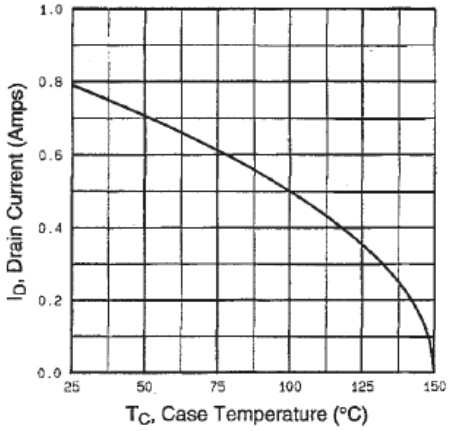



Fig. 9 - Maximum Drain Current vs. Case Temperature

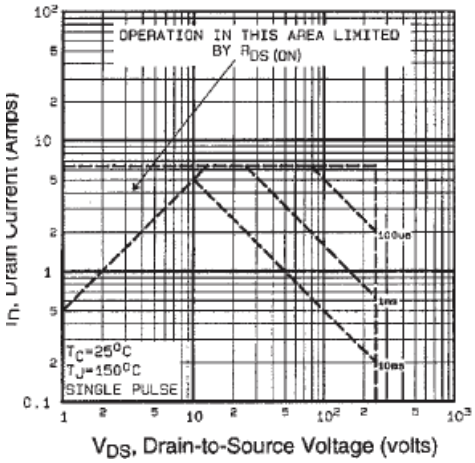



Fig. 8 - Maximum Safe Operating Area

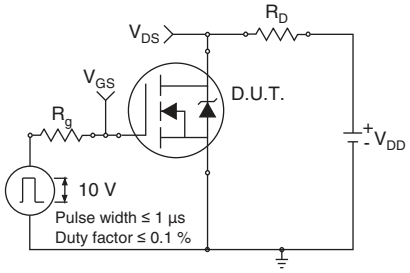



Fig. 10a - Switching Time Test Circuit

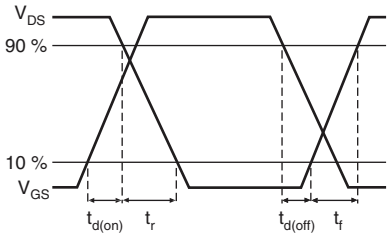



Fig. 10b - Switching Time Waveforms

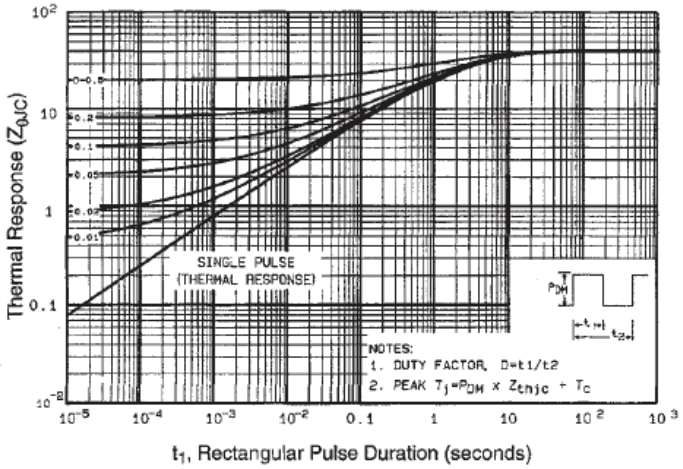



Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

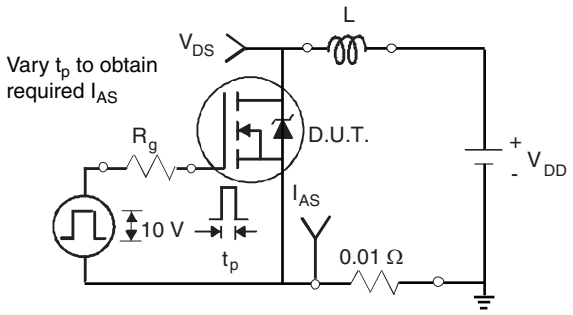



Fig. 12a - Unclamped Inductive Test Circuit

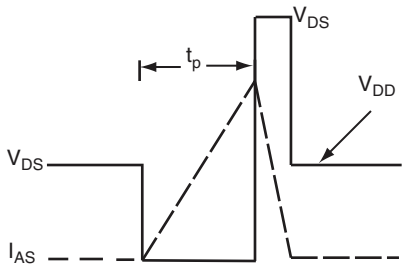



Fig. 12b - Unclamped Inductive Waveforms

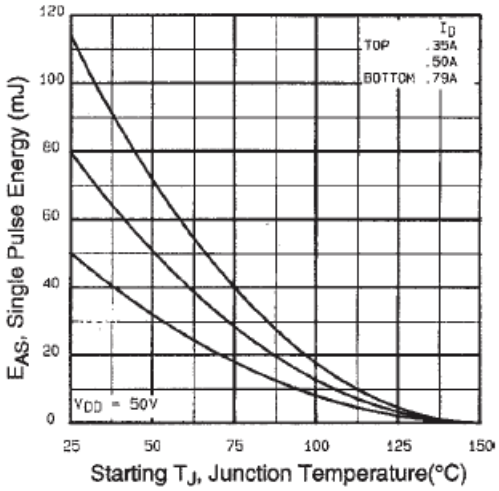



Fig. 12c - Maximum Avalanche Energy vs. Drain Current

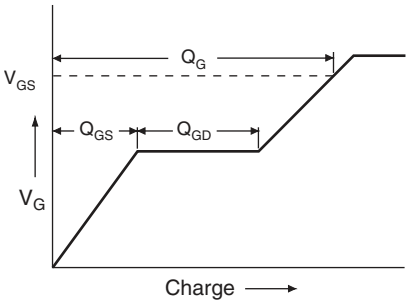



Fig. 13a - Basic Gate Charge Waveform

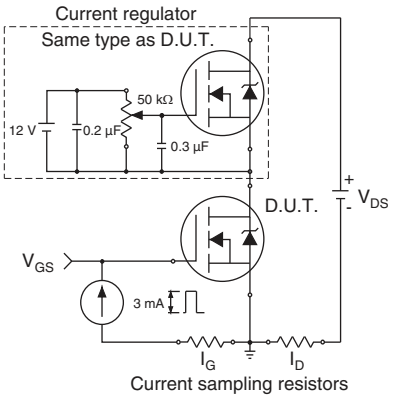
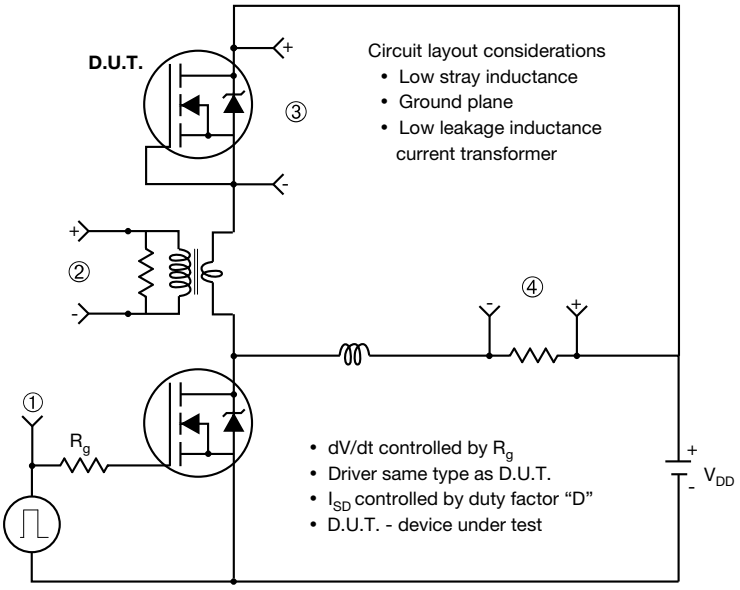
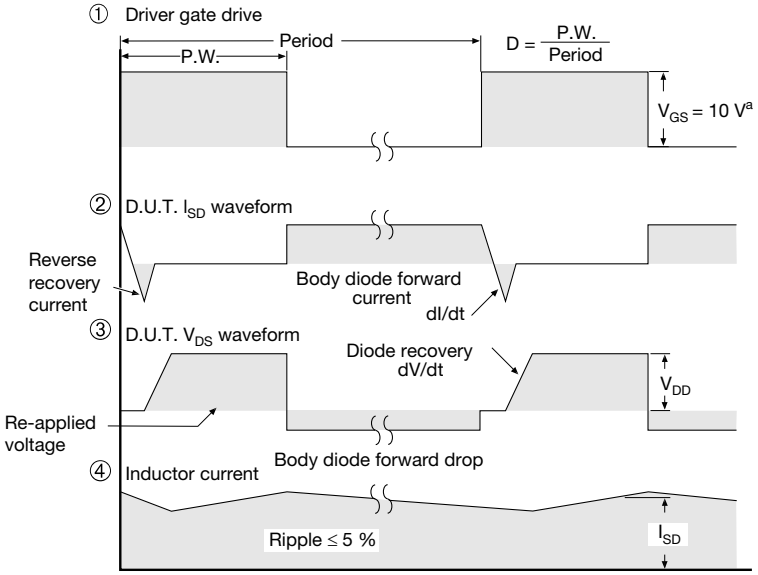



Fig. 13b - Gate Charge Test Circuit

**Peak Diode Recovery dV/dt Test Circuit**



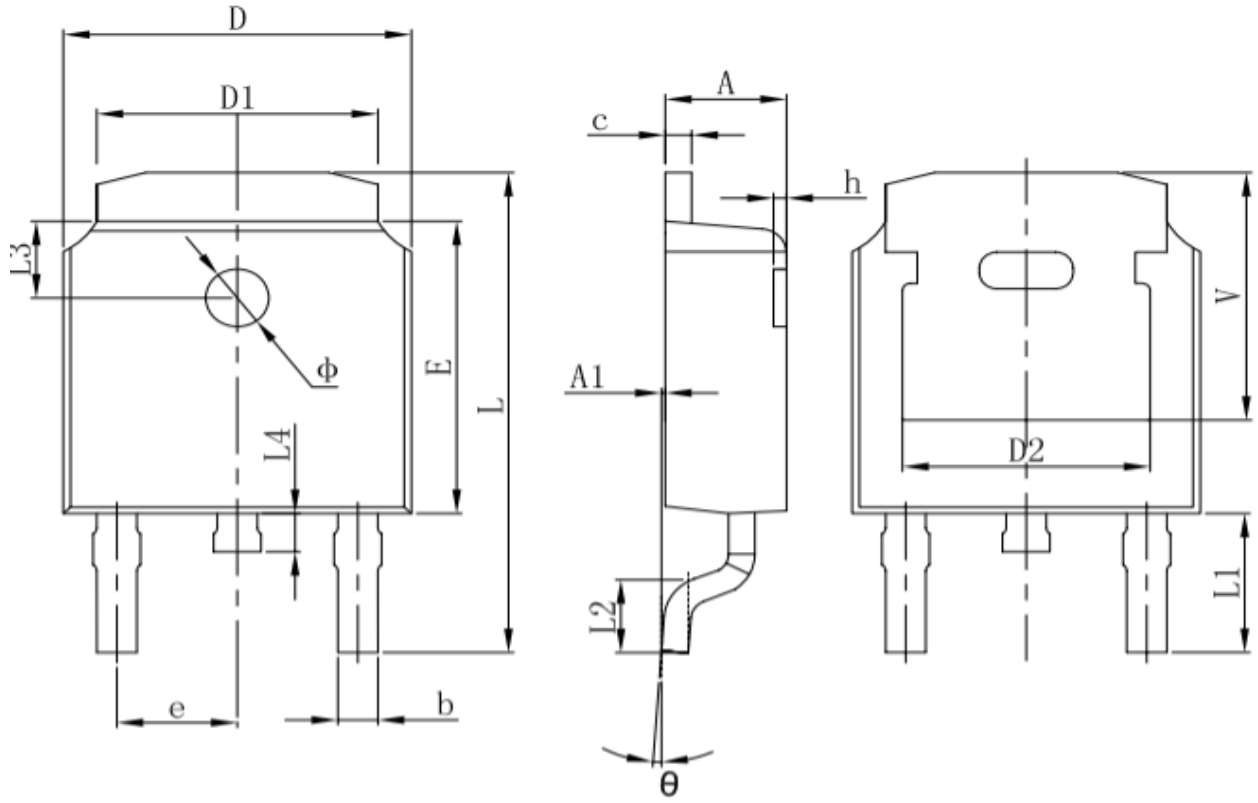




**Note**

a. $V_{GS}$ = 5 V for logic level devices

**Fig.14 - For N-Channel**

# TO252 Package Information




| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|---|---|---|---|---|
| | Min. | Max. | Min. | Max. |
| A | 2.200 | 2.400 | 0.087 | 0.094 |
| A1 | 0.000 | 0.127 | 0.000 | 0.005 |
| b | 0.635 | 0.770 | 0.025 | 0.030 |
| c | 0.460 | 0.580 | 0.018 | 0.023 |
| D | 6.500 | 6.700 | 0.256 | 0.264 |
| D1 | 5.100 | 5.460 | 0.201 | 0.215 |
| D2 | 4.830 REF. | | 0.190 REF. | |
| E | 6.000 | 6.200 | 0.236 | 0.244 |
| e | 2.186 | 2.386 | 0.086 | 0.094 |
| L | 9.712 | 10.312 | 0.382 | 0.406 |
| L1 | 2.900 REF. | | 0.114 REF. | |
| L2 | 1.400 | 1.700 | 0.055 | 0.067 |
| L3 | 1.600 REF. | | 0.063 REF. | |
| L4 | 0.600 | 1.000 | 0.024 | 0.039 |
| Φ | 1.100 | 1.300 | 0.043 | 0.051 |
| θ | 0° | 8° | 0° | 8° |
| h | 0.000 | 0.300 | 0.000 | 0.012 |
| V | 5.250 REF. | | 0.207 REF. | |

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